

150V breakdown voltage half bridge pre-driver IC SPF6001 (Auxiliary power mounted)

■ Features

- 150V breakdown voltage bootstrap circuit drive system
- Charge pump circuit/Auxiliary power mounted
- Sanken original power surface mount
- Absolute maximum ratings

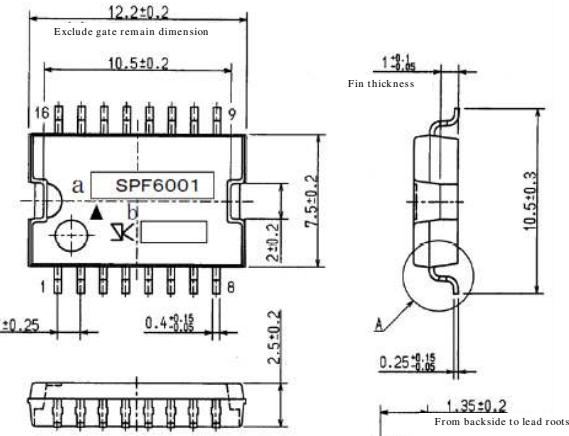
Item	Symbol	Ratings	Unit	Remark
DC input voltage	VBB	-0.6 ~ -35	V	40V T<400mS
VREG Power supply voltage for gate pin control	VREG	-0.6 ~ 18	V	
Power supply voltage for logic circuit	VDD	-0.3 ~ 6	V	
Input pin control voltage	HLO,EN	-0.3 ~ 6	V	
LS LS pin breakdown voltage	LS	-4 ~ -4	V	
LS GL pin breakdown voltage	GL	-4 ~ -18	V	
H/S S pin breakdown voltage	S	-4 ~ -110	V	
H/S GH pin breakdown voltage	GH	-4 ~ -110	V	
H/S C pin breakdown voltage	C	-0.3 ~ -110	V	
FLT pin breakdown voltage	VFLT	-0.3 ~ -6	V	
CPI pin breakdown voltage	CPI	-0.3 ~ -18	V	
CP2 pin breakdown voltage	CP2	-0.3 ~ -18	V	
Power dissipation	PDI	18.6	W	With infinite heat sink
	PD2	2.97	W	*1
Junction temperature	Tj	-40 ~ 150	°C	
Operating ambient temperature	Top	-40 ~ 105	°C	
Storage temperature	Tstg	-40 ~ 150	°C	
Thermal resistance (Junction to Case)	θj-C	6.7	°C/W	
Thermal resistance (Junction to Ambient)	θj-a	42	°C/W	

*1 When use glass epoxy + copper foil board (Size: 5.0×7.4cm, t: glass epoxy=1.6mm, copper foil=18μm)

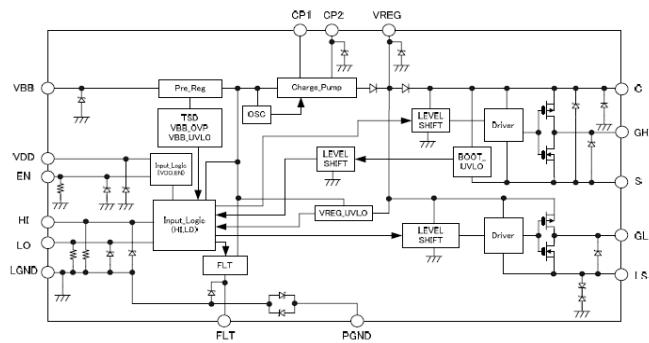
■ Electrical characteristics (Tj=25°C)

Tj=30~125°C, VBB=14V,VDD=EN=5V,Creg=10pF,f PWM=22.5KHz,CP=0.1pF,CBOOT=0.1pF, unless otherwise specified							
Characteristic	Symbol	Limits			Unit	Test Conditions	
		MIN	Typ	MAX			
Input power supply voltage	VBB	7	14	18	V	-	
	VDD	4.5	5	5.5	V	-	
VBB input current	IBB1	-	3	-	mA	VDD=EN=0V, HI=LO=0V with steady state (No load)	
	IBB2	-	4	-	mA	HI=LO=0V with steady state (No load)	
VDD input current	IDD	-	1.0	5.0	mA	HI=LO=0V with steady state (No load)	
C,GH,S,LGND current	ICL	-	100	100	μA	C=GH=S=LGND	
VREG output voltage	VREG1	6	12	18	V	7V≤VBB<8V	
	VREG2	12	15	18	V	8V≤VBB	
EN pin • Input control voltage	VENH	2.0	-	-	V	HI=5V,LS=S=LGND	
	VENL	-	0.8	-	V	After input EN, LO=0V→5V (GL monitor)	
	AEN	-	0.15	-	V	-	
HI,LO pin • Input control voltage	VhH	2.0	-	-	V	LO=5V,LS=S=LGND	
	VhL	-	0.8	-	V	After input EN, HI=0V→5V (GH monitor)	
	AlH	-	0.15	-	V	-	
	VlH	2.0	-	-	V	HI=5V,LS=S=LGND	
	VlL	-	0.8	-	V	HI=0V,LS=S=LGND	
EN pin • Input control current	IENH	-	100	500	μA	EN=5V	
	IENL	-100	-	-	μA	EN=0V	
HI,LO pin • Input control current	ihuH	-	100	500	μA	HI=5V	
	ihuL	-100	-	-	μA	HI=0V	
HI,LO pin • Input control current	iluH	-	100	500	μA	LO=5V	
	iluL	-100	-	-	μA	LO=0V	
FLT pin • Output saturation voltage	VFLT	-	-	0.4	V	IGTL=1mA	
Boot Strap Di Vth	BDiVth	0.4	1.2	1.7	V	-	
GH pin • Source RDS(ON)H	RDSsG _H	6	9	15	Ω	HI=5V,LO=0V,LS=S=LGND,C>10V,VREG>10V	
GH pin • Sink RDS(ON)H	RDSsG _H	4	6	10	Ω	HI=5V,LO=0V,LS=S=LGND,C>10V,VREG>10V	
GH pin • start-up time	t _{rGH}	10	50	100	nS	VGH=20%→80%,Ciss=3300pF	
GH pin • falling time	t _{fGH}	10	50	100	nS	VGH=80%→20%,Ciss=3300pF	
GL pin • Source RDS(ON)L	RDSsG _L	6	9	15	Ω	HI=0V,LO=5V,LS=S=LGND,C>10V,VREG>10V	
GL pin • Sink RDS(ON)L	RDSsG _L	4	6	10	Ω	HI=0V,LO=5V,LS=S=LGND,C>10V,VREG>10V	
GL pin • start-up time	t _{rGL}	10	50	100	nS	VGL=20%→80%,Ciss=3300pF	
GL pin • falling time	t _{fGL}	10	50	100	nS	VGL=80%→20%,Ciss=3300pF	
Output delay time	t _{onH}	150	250	420	nS	VhiH=VGH=10%,Ciss=3300pF	
	t _{offH}	150	250	410	nS	VhiH=VGH=80%,Ciss=3300pF	
	t _{onL}	150	250	420	nS	Viol=VGH=10%,Ciss=3300pF	
	t _{offL}	150	250	410	nS	Viol=VGH=90%,Ciss=3300pF	
VDD UVLO releasing voltage	VuvddH	3.5	4.0	4.5	V	(GH,GL,FLT monitor)	
VDD UVLO activating voltage	VuvddL	3.3	3.8	4.3	V	(GH,GL,FLT monitor)	
VDD UVLO hysteresis	ΔVuvdd	-	200	-	mV		
VBB OVP releasing voltage	VovbbH	24	28	32	V	(GH,GL,FLT monitor)	
VBB OVF activating voltage	VovbbL	22	25	31	V		
VBB UVLO releasing voltage	Vurbbh	-	3	-	V		
VBB UVLO activating voltage	Vurbbl	6.0	6.5	7.0	V	(GH,GL,FLT monitor)	
VBB UVLO hysteresis	ΔVurbb	-	5.5	6.1	6.6	V	

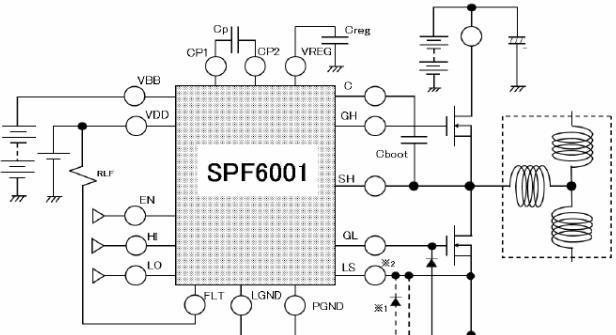
■ Package



■ Circuit block diagram



■ Typical connection diagram



■ Timing chart

